

Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101fcdfp-v0

Table 1-1. List of Ordering Part Numbers

(9/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAB#V0, R5F100LDAB#V0, R5F100LEAB#V0, R5F100LFAB#V0, R5F100LGAB#V0, R5F100LHAB#V0, R5F100LJAB#V0, R5F100LKAB#V0, R5F100LLAB#V0 R5F100LCAB#X0, R5F100LDAB#X0, R5F100LEAB#X0, R5F100LFAB#X0, R5F100LGAB#X0, R5F100LHAB#X0, R5F100LJAB#X0, R5F100LKAB#X0, R5F100LLAB#X0 R5F100LCD#V0, R5F100LDD#V0, R5F100LED#V0, R5F100LFDF#V0, R5F100LGDF#V0, R5F100LHD#V0, R5F100LJD#V0, R5F100LKDF#V0, R5F100LLD#V0 R5F100LCD#X0, R5F100LDD#X0, R5F100LED#X0, R5F100LFDF#X0, R5F100LGDF#X0, R5F100LHD#X0, R5F100LJD#X0, R5F100LKDF#X0, R5F100LLD#X0 R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0 R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
			D	
			G	
			A	R5F101LCAB#V0, R5F101LDAB#V0, R5F101LEAB#V0, R5F101LFAB#V0, R5F101LGAB#V0, R5F101LHAB#V0, R5F101LJAB#V0, R5F101LKAB#V0, R5F101LLAB#V0 R5F101LCAB#X0, R5F101LDAB#X0, R5F101LEAB#X0, R5F101LFAB#X0, R5F101LGAB#X0, R5F101LHAB#X0, R5F101LJAB#X0, R5F101LKAB#X0, R5F101LLAB#X0 R5F101LCD#V0, R5F101LDD#V0, R5F101LED#V0, R5F101LFDF#V0, R5F101LGDF#V0, R5F101LHD#V0, R5F101LJD#V0, R5F101LKDF#V0, R5F101LLD#V0 R5F101LCD#X0, R5F101LDD#X0, R5F101LED#X0, R5F101LFDF#X0, R5F101LGDF#X0, R5F101LHD#X0, R5F101LJD#X0, R5F101LKDF#X0, R5F101LLD#X0
			D	
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0 R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGBBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0 R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGBBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
			G	
			A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0
			Not mounted	

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

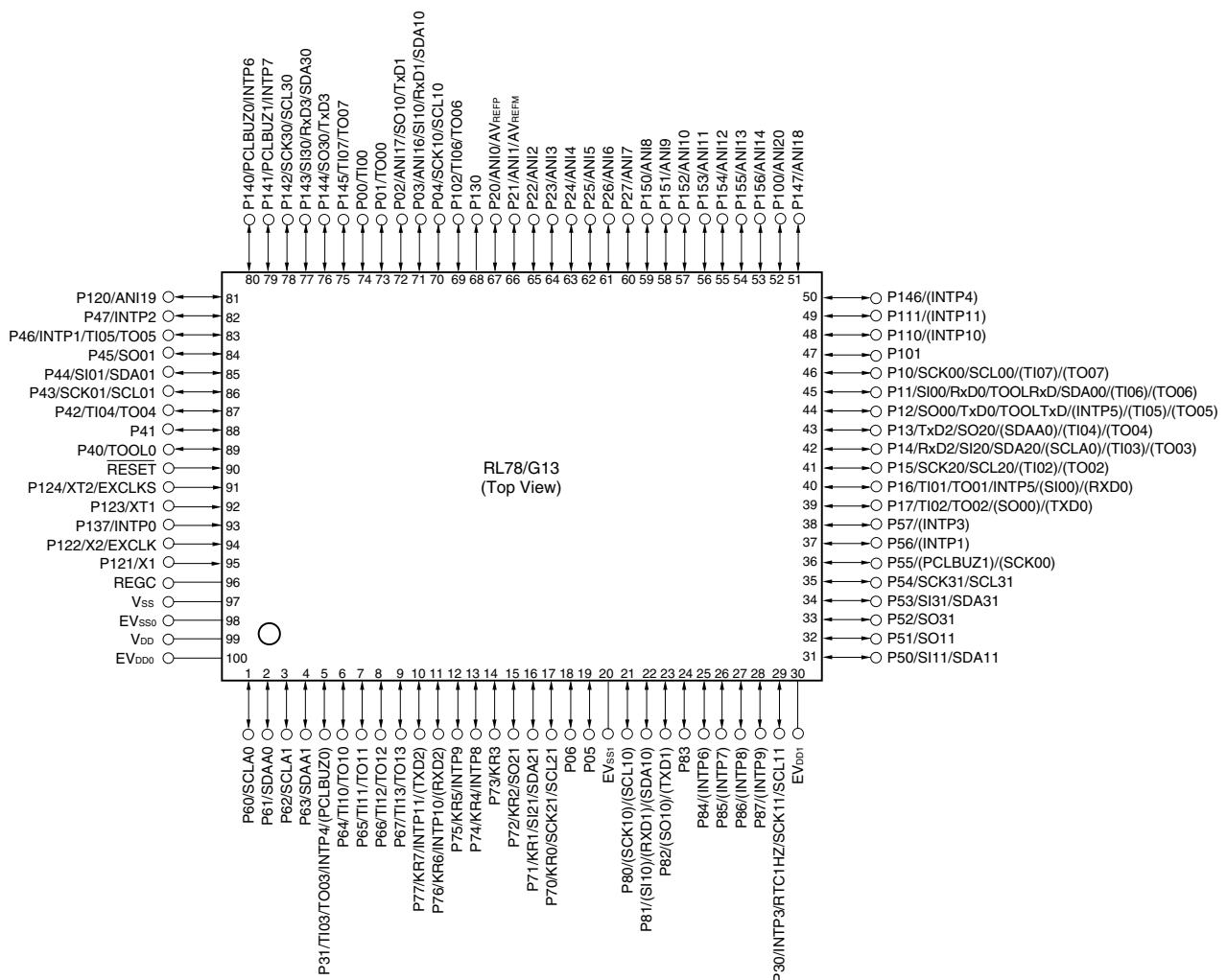
(10/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0 R5F100MF DFA#V0, R5F100MG DFA#V0, R5F100MH DFA#V0, R5F100MJ DFA#V0, R5F100MK DFA#V0, R5F100ML DFA#V0 R5F100MF DFA#X0, R5F100MG DFA#X0, R5F100MH DFA#X0, R5F100MJ DFA#X0, R5F100MK DFA#X0, R5F100ML DFA#X0 R5F100MFGFA#V0, R5F100MG GFA#V0, R5F100MH GFA#V0, R5F100MJ GFA#V0 R5F100MFGFA#X0, R5F100MG GFA#X0, R5F100MH GFA#X0, R5F100MJ GFA#X0
			D	
			G	
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MHAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0 R5F101MF DFA#V0, R5F101MG DFA#V0, R5F101MH DFA#V0, R5F101MJ DFA#V0, R5F101MK DFA#V0, R5F101ML DFA#V0 R5F101MF DFA#X0, R5F101MG DFA#X0, R5F101MH DFA#X0, R5F101MJ DFA#X0, R5F101MK DFA#X0, R5F101ML DFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MHAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0 R5F100MF DFB#V0, R5F100MG DFB#V0, R5F100MH DFB#V0, R5F100MJ DFB#V0, R5F100MK DFB#V0, R5F100ML DFB#V0 R5F100MF DFB#X0, R5F100MG DFB#X0, R5F100MH DFB#X0, R5F100MJ DFB#X0, R5F100MK DFB#X0, R5F100ML DFB#X0 R5F100MFGFB#V0, R5F100MG GFB#V0, R5F100MH GFB#V0, R5F100MJ GFB#V0 R5F100MFGFB#X0, R5F100MG GFB#X0, R5F100MH GFB#X0, R5F100MJ GFB#X0
			D	
			G	
		Not mounted	A	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MLAFB#V0 R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0 R5F101MF DFB#V0, R5F101MG DFB#V0, R5F101MH DFB#V0, R5F101MJ DFB#V0, R5F101MK DFB#V0, R5F101ML DFB#V0 R5F101MF DFB#X0, R5F101MG DFB#X0, R5F101MH DFB#X0, R5F101MJ DFB#X0, R5F101MK DFB#X0, R5F101ML DFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



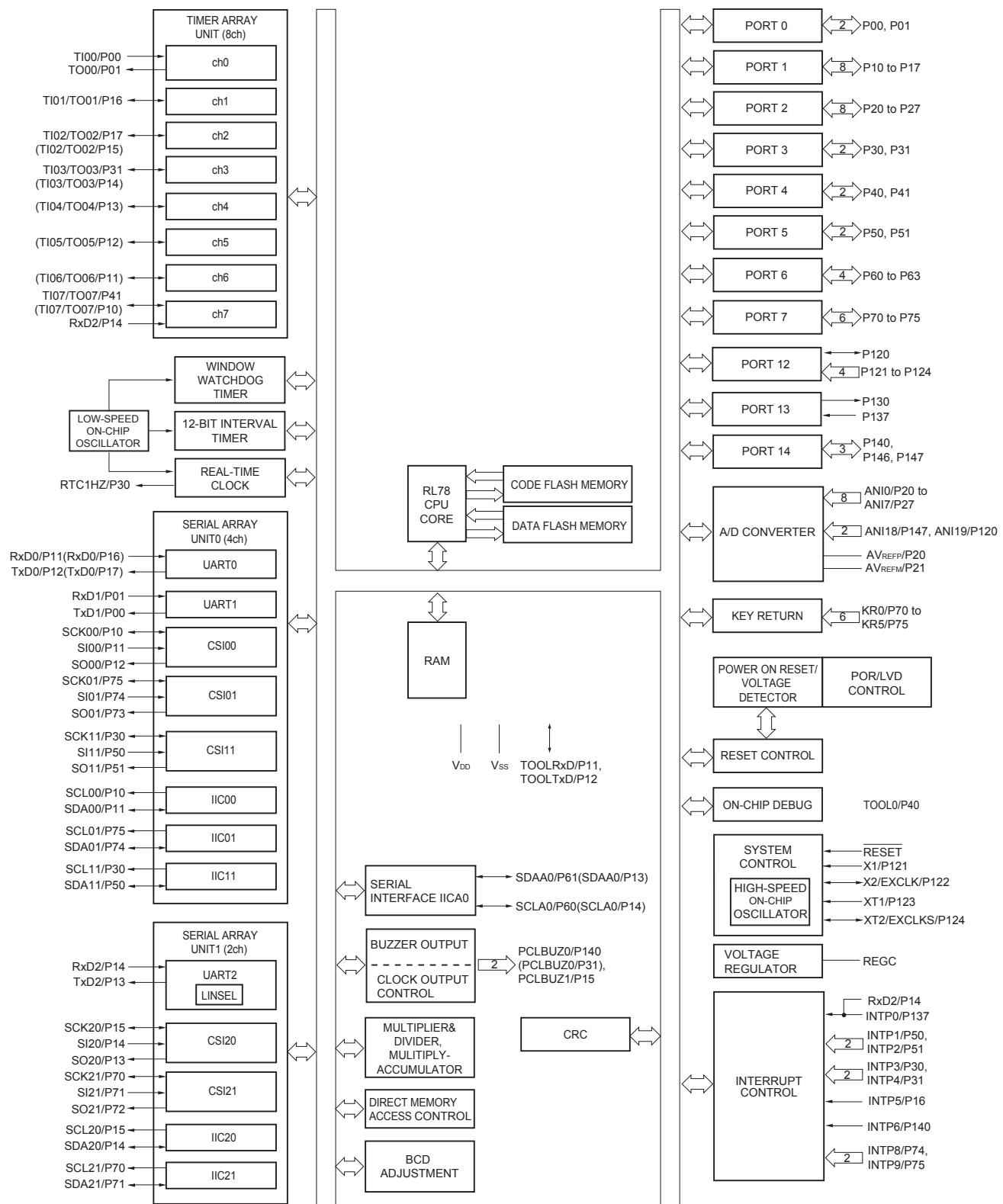
Cautions 1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

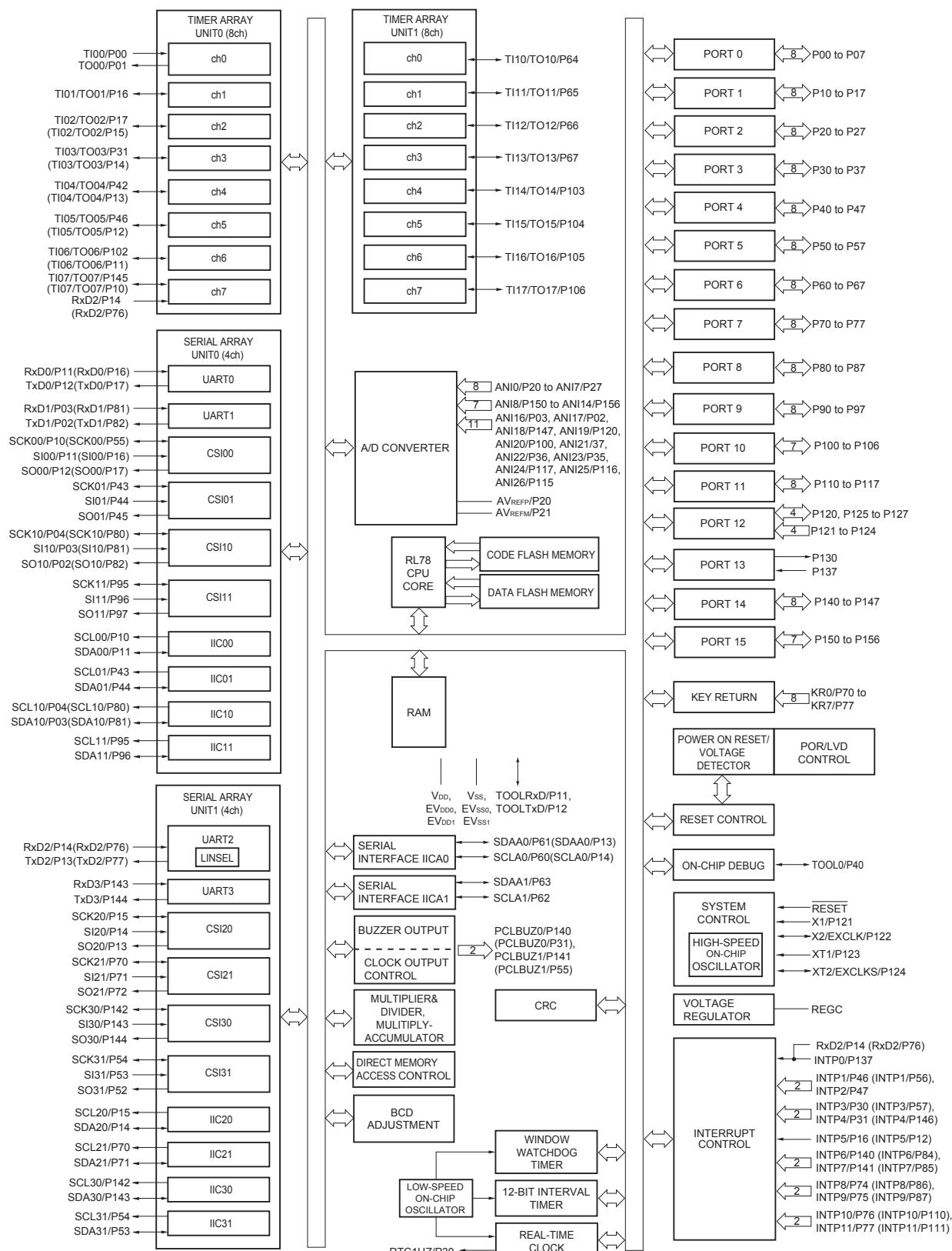
2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item	80-pin		100-pin		128-pin										
	R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx									
Code flash memory (KB)	96 to 512		96 to 512		192 to 512										
Data flash memory (KB)	8	—	8	—	8	—									
RAM (KB)	8 to 32 ^{Note 1}		8 to 32 ^{Note 1}		16 to 32 ^{Note 1}										
Address space	1 MB														
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)													
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)													
Subsystem clock	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz														
Low-speed on-chip oscillator	15 kHz (TYP.)														
General-purpose register	(8-bit register × 8) × 4 banks														
Minimum instruction execution time	0.03125 μ s (High-speed on-chip oscillator: $f_{IH} = 32$ MHz operation)														
	0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)														
	30.5 μ s (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)														
Instruction set	<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 														
I/O port	Total	74	92	120											
	CMOS I/O	64 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 21)	82 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 24)	110 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 25)											
	CMOS input	5	5	5											
	CMOS output	1	1	1											
	N-ch O.D. I/O (withstand voltage: 6 V)	4	4	4											
Timer	16-bit timer	12 channels	12 channels	16 channels											
	Watchdog timer	1 channel	1 channel	1 channel											
	Real-time clock (RTC)	1 channel	1 channel	1 channel											
	12-bit interval timer (IT)	1 channel	1 channel	1 channel											
	Timer output	12 channels (PWM outputs: 10 ^{Note 2})	12 channels (PWM outputs: 10 ^{Note 2})	16 channels (PWM outputs: 14 ^{Note 2})											
	RTC output	1 channel • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)													

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator and subsystem clock are stopped.
4. When high-speed system clock and subsystem clock are stopped.
5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz
 $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH} : High-speed on-chip oscillator clock frequency

3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{ss} = EV_{ss0} = EV_{ss1} = 0 \text{ V}$) (2/2)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Supply current <small>Note 1</small>	$I_{DD2}^{Note 2}$	HALT mode	HS (high-speed main) mode ^{Note 7}	$f_{IH} = 32 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 \text{ V}$		0.62	1.89 mA
				$V_{DD} = 3.0 \text{ V}$			0.62	1.89 mA
			$f_{IH} = 24 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 \text{ V}$		0.50	1.48	mA
				$V_{DD} = 3.0 \text{ V}$		0.50	1.48	mA
			$f_{IH} = 16 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 \text{ V}$		0.44	1.12	mA
				$V_{DD} = 3.0 \text{ V}$		0.44	1.12	mA
		LS (low-speed main) mode ^{Note 7}	$f_{IH} = 8 \text{ MHz}^{Note 4}$	$V_{DD} = 3.0 \text{ V}$		290	620	μA
				$V_{DD} = 2.0 \text{ V}$		290	620	μA
		LV (low-voltage main) mode <small>Note 7</small>	$f_{IH} = 4 \text{ MHz}^{Note 4}$	$V_{DD} = 3.0 \text{ V}$		460	700	μA
				$V_{DD} = 2.0 \text{ V}$		460	700	μA
		HS (high-speed main) mode ^{Note 7}	$f_{MX} = 20 \text{ MHz}^{Note 3}$, $V_{DD} = 5.0 \text{ V}$	Square wave input		0.31	1.14	mA
				Resonator connection		0.48	1.34	mA
			$f_{MX} = 20 \text{ MHz}^{Note 3}$, $V_{DD} = 3.0 \text{ V}$	Square wave input		0.31	1.14	mA
				Resonator connection		0.48	1.34	mA
			$f_{MX} = 10 \text{ MHz}^{Note 3}$, $V_{DD} = 5.0 \text{ V}$	Square wave input		0.21	0.68	mA
				Resonator connection		0.28	0.76	mA
			$f_{MX} = 10 \text{ MHz}^{Note 3}$, $V_{DD} = 3.0 \text{ V}$	Square wave input		0.21	0.68	mA
				Resonator connection		0.28	0.76	mA
		LS (low-speed main) mode ^{Note 7}	$f_{MX} = 8 \text{ MHz}^{Note 3}$, $V_{DD} = 3.0 \text{ V}$	Square wave input		110	390	μA
				Resonator connection		160	450	μA
			$f_{MX} = 8 \text{ MHz}^{Note 3}$, $V_{DD} = 2.0 \text{ V}$	Square wave input		110	390	μA
				Resonator connection		160	450	μA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = -40^\circ\text{C}$	Square wave input		0.31	0.66	μA
				Resonator connection		0.50	0.85	μA
			$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = +25^\circ\text{C}$	Square wave input		0.38	0.66	μA
				Resonator connection		0.57	0.85	μA
			$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = +50^\circ\text{C}$	Square wave input		0.47	3.49	μA
				Resonator connection		0.66	3.68	μA
			$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = +70^\circ\text{C}$	Square wave input		0.80	6.10	μA
				Resonator connection		0.99	6.29	μA
			$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = +85^\circ\text{C}$	Square wave input		1.52	10.46	μA
				Resonator connection		1.71	10.65	μA
		$I_{DD3}^{Note 6}$	STOP mode ^{Note 8}	$T_A = -40^\circ\text{C}$		0.19	0.54	μA
				$T_A = +25^\circ\text{C}$		0.26	0.54	μA
				$T_A = +50^\circ\text{C}$		0.35	3.37	μA
				$T_A = +70^\circ\text{C}$		0.68	5.98	μA
				$T_A = +85^\circ\text{C}$		1.40	10.34	μA

(Notes and Remarks are listed on the next page.)

2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	TCY	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem clock (f _{SUB}) operation		1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V			1.0		4.0	MHz
	f _{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V _{DD} < 2.7 V			30			ns
		1.8 V ≤ V _{DD} < 2.4 V			60			ns
		1.6 V ≤ V _{DD} < 1.8 V			120			ns
	t _{EXHS} , t _{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t _{TIH} , t _{TL}				1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			1.8 V ≤ EV _{DD0} < 2.7 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
		LS (low-speed main) mode	1.8 V ≤ EV _{DD0} ≤ 5.5 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EV _{DD0} ≤ 5.5 V				2	MHz
		HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			1.8 V ≤ EV _{DD0} < 2.7 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	LS (low-speed main) mode	1.8 V ≤ EV _{DD0} ≤ 5.5 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
			1.8 V ≤ EV _{DD0} ≤ 5.5 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EV _{DD0} ≤ 5.5 V				4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V				2	MHz
			1.8 V ≤ EV _{DD0} ≤ 5.5 V				4	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	1.6 V ≤ V _{DD} ≤ 5.5 V	1				μs
		INTP1 to INTP11	1.6 V ≤ EV _{DD0} ≤ 5.5 V	1				μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	1.8 V ≤ EV _{DD0} ≤ 5.5 V	250				ns
			1.6 V ≤ EV _{DD0} < 1.8 V	1				μs
RESET low-level width	t _{RSR}				10			μs

(Note and Remark are listed on the next page.)

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp \uparrow) <small>Note 1</small>	t _{SIK2}	2.7 V \leq EV _{DD0} \leq 5.5 V	1/f _{MCK} +20		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V	1/f _{MCK} +30		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.7 V \leq EV _{DD0} \leq 5.5 V	1/f _{MCK} +40		1/f _{MCK} +40		1/f _{MCK} +40		ns
		1.6 V \leq EV _{DD0} \leq 5.5 V	—		1/f _{MCK} +40		1/f _{MCK} +40		ns
Slp hold time (from SCKp \uparrow) <small>Note 2</small>	t _{KSI2}	1.8 V \leq EV _{DD0} \leq 5.5 V	1/f _{MCK} +31		1/f _{MCK} +31		1/f _{MCK} +31		ns
		1.7 V \leq EV _{DD0} \leq 5.5 V	1/f _{MCK} +250		1/f _{MCK} +250		1/f _{MCK} +250		ns
		1.6 V \leq EV _{DD0} \leq 5.5 V	—		1/f _{MCK} +250		1/f _{MCK} +250		ns
Delay time from SCKp \downarrow to SO _p output <small>Note 3</small>	t _{KSO2}	C = 30 pF <small>Note 4</small>	2.7 V \leq EV _{DD0} \leq 5.5 V		2/f _{MCK} +44		2/f _{MCK} +110		2/f _{MCK} +110
			2.4 V \leq EV _{DD0} \leq 5.5 V		2/f _{MCK} +75		2/f _{MCK} +110		2/f _{MCK} +110
			1.8 V \leq EV _{DD0} \leq 5.5 V		2/f _{MCK} +110		2/f _{MCK} +110		2/f _{MCK} +110
			1.7 V \leq EV _{DD0} \leq 5.5 V		2/f _{MCK} +220		2/f _{MCK} +220		2/f _{MCK} +220
			1.6 V \leq EV _{DD0} \leq 5.5 V		—		2/f _{MCK} +220		2/f _{MCK} +220

- Notes**
- When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp setup time becomes “to SCKp \downarrow ” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 - When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp hold time becomes “from SCKp \downarrow ” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 - When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The delay time to SO_p output becomes “from SCKp \uparrow ” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 - C is the load capacitance of the SO_p output lines.
 - Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SO_p pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(5) During communication at same potential (simplified I²C mode) (2/2)(TA = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 85 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 230 Note2		1/f _{MCK} + 230 Note2		1/f _{MCK} + 230 Note2		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		ns
Data hold time (transmission)	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Set the f_{MCK} value to keep the hold time of SCL_r = "L" and SCL_r = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCL_r pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

(TA = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate	Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{\text{Note 4}}$	f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		bps
				f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		Mbps
				f _{MCK} /6 Notes 1 to 3		f _{MCK} /6 Notes 1, 2		f _{MCK} /6 Notes 1, 2		bps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. Use it with EV_{DD0} ≥ V_b.
3. The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.
 - 2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps
 - 1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps
4. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (2/2)

($T_A = -40$ to $+85^\circ\text{C}$, $2.7 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp \downarrow) ^{Note 2}	tsIK1	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 20 pF, R _b = 1.4 k Ω	23		110		110		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 20 pF, R _b = 2.7 k Ω	33		110		110		ns
Slp hold time (from SCKp \downarrow) ^{Note 2}	tKSI1	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 20 pF, R _b = 1.4 k Ω	10		10		10		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 20 pF, R _b = 2.7 k Ω	10		10		10		ns
Delay time from SCKp \uparrow to SO _p output ^{Note 2}	tKS01	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 20 pF, R _b = 1.4 k Ω		10		10		10	ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 20 pF, R _b = 2.7 k Ω		10		10		10	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. R_b[Ω]:Communication line (SCKp, SO_p) pull-up resistance, C_b[F]: Communication line (SCKp, SO_p) load capacitance, V_b[V]: Communication line voltage

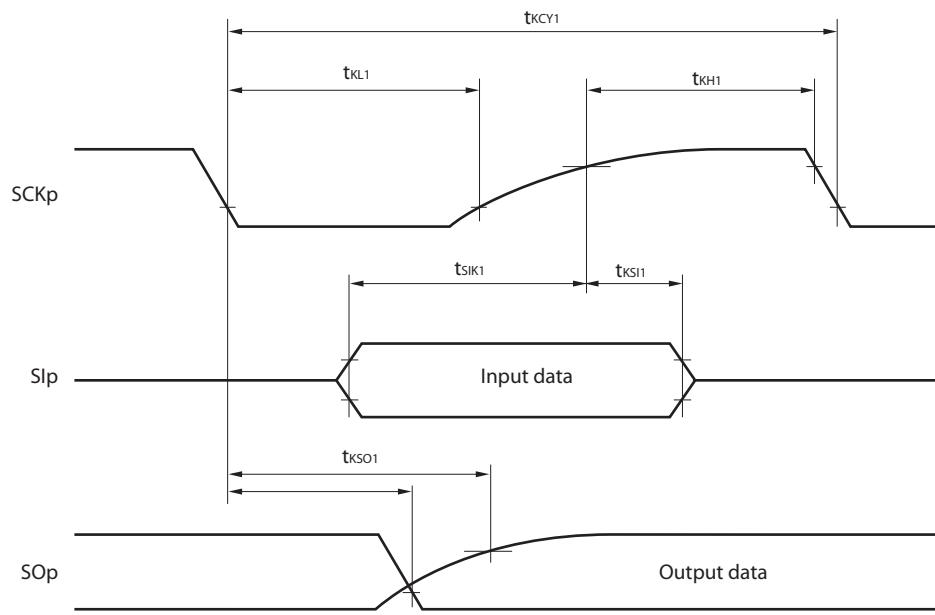
2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency

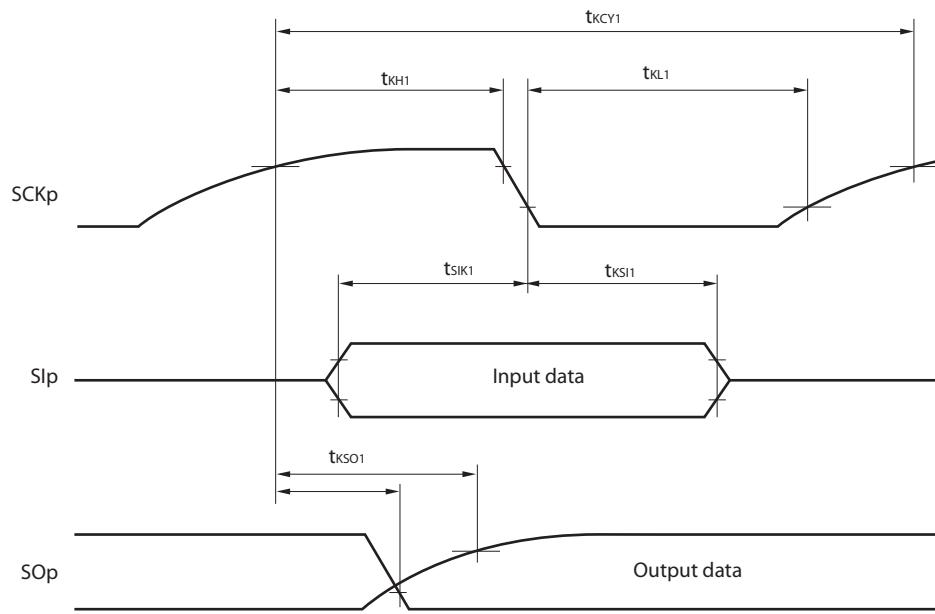
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 0$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 1$.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 1$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 0$.)



- Remarks**
1. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number, n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

(3) I²C fast mode plus $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode plus: $f_{CLK} \geq 10 \text{ MHz}$	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$	0	1000	—	—	—	—	kHz
Setup time of restart condition	t _{SU:STA}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.26		—	—	—	—	μs
Hold time ^{Note 1}	t _{HD:STA}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.26		—	—	—	—	μs
Hold time when SCLA0 = "L"	t _{LOW}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.5		—	—	—	—	μs
Hold time when SCLA0 = "H"	t _{HIGH}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.26		—	—	—	—	μs
Data setup time (reception)	t _{SU:DAT}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		50		—	—	—	—	μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0	0.45	—	—	—	—	μs
Setup time of stop condition	t _{SU:STO}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.26		—	—	—	—	μs
Bus-free time	t _{BUF}	$2.7 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$		0.5		—	—	—	—	μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

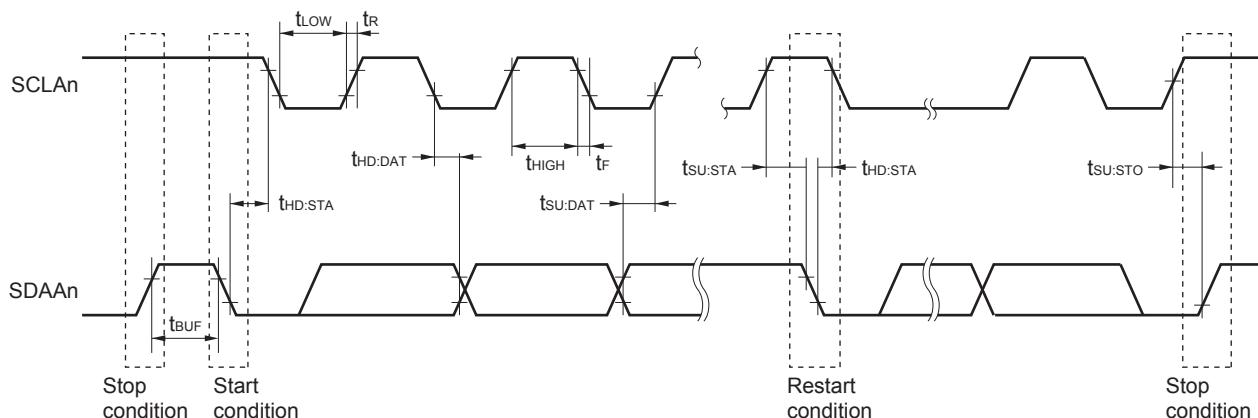
<R> 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω

IICA serial transfer timing



Remark n = 0, 1

- (3) When reference voltage (+) = V_{DD} ($\text{ADREFP1} = 0$, $\text{ADREFP0} = 0$), reference voltage (-) = V_{SS} ($\text{ADREFM} = 0$), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$		1.2	± 7.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3		1.2	± 10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 4.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 2.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{IH} = 32 \text{ MHz}$ ^{Note 3}	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 5.0 \text{ V}$		5.2	9.2	mA
				$f_{IH} = 24 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 3.0 \text{ V}$		5.2	9.2	mA
					Normal operation	$V_{DD} = 5.0 \text{ V}$		4.1	7.0	mA
				$f_{IH} = 16 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 3.0 \text{ V}$		4.1	7.0	mA
					Normal operation	$V_{DD} = 5.0 \text{ V}$		3.0	5.0	mA
		HS (high-speed main) mode Note 5	$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
			$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9		μA
				Normal operation	Resonator connection		4.9	6.0		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.9	5.9		μA
				Normal operation	Resonator connection		5.0	6.0		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6		μA
				Normal operation	Resonator connection		5.1	7.7		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3		μA
				Normal operation	Resonator connection		5.3	9.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3		μA
				Normal operation	Resonator connection		5.8	13.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +105^\circ\text{C}$	Normal operation	Square wave input		10.0	46.0		μA
				Normal operation	Resonator connection		10.0	46.0		μA

(Notes and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{ss} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode	Unit
		MIN.	MAX.		
SCKp cycle time	t _{KCY1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	600		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	1000		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	2300		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 150		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 340		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 916		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 24		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 36		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 100		ns

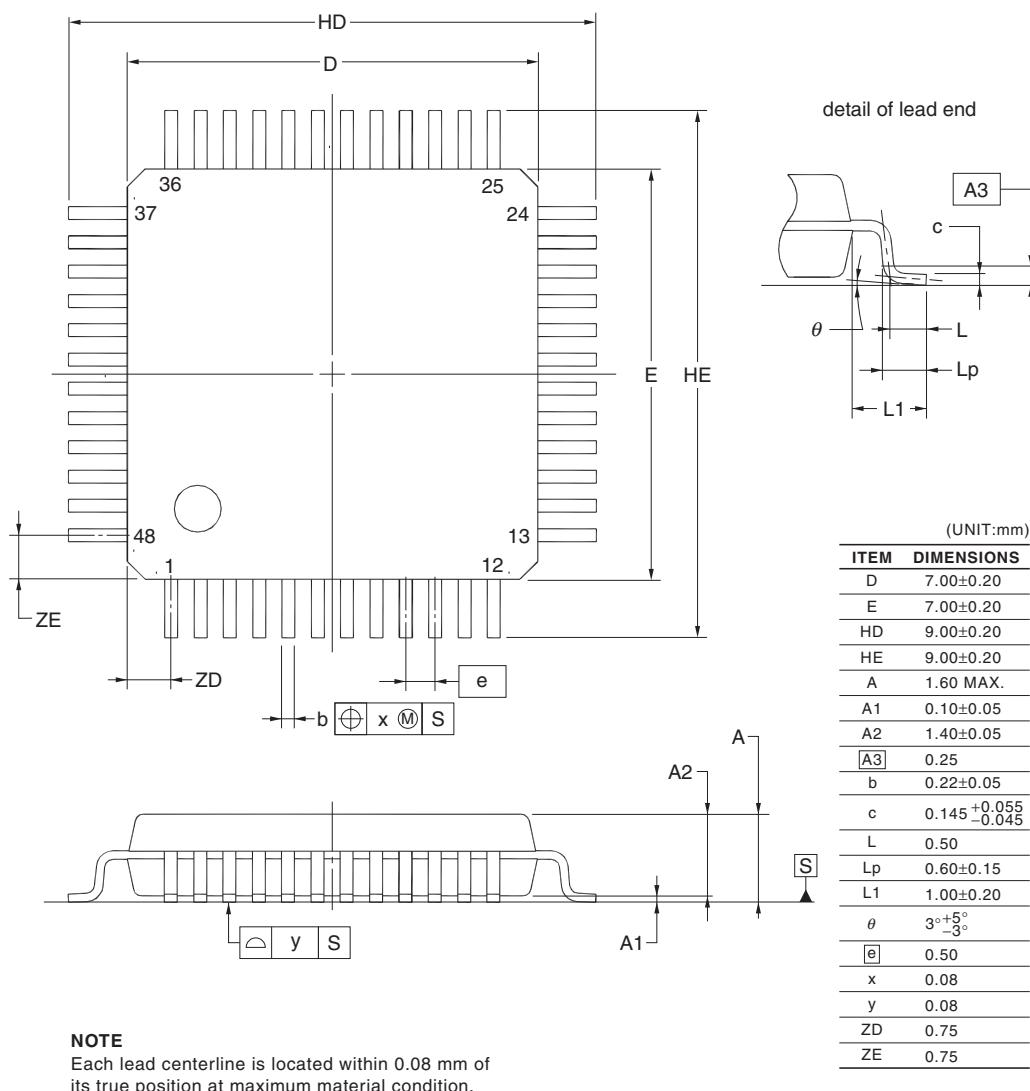
Caution Select the TTL input buffer for the S_lp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

4.9 48-pin Products

R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GGAFB,
 R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB
 R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GGAFB,
 R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB
 R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GGDFB,
 R5F100GHDDB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB
 R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GGDFB,
 R5F101GHDDB, R5F101GJDFB, R5F101GKDFB, R5F101GLDFB
 R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GGGFB,
 R5F100GHGFB, R5F100GJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16



Revision History		RL78/G13 Data Sheet	
Rev.	Date	Description	
		Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing